

SGM42609 Single H-Bridge Motor Driver

GENERAL DESCRIPTION

The SGM42609 provides a single bridge motor driver solution for battery-powered toys, toothbrushes and other low-voltage or battery-powered motion control applications. The device has one H-bridge driver, and can drive one DC brush motor, solenoid, or other inductive load.

The output driver block of H-bridge consists of N-channel power MOSFETs configured as an H-bridge to drive the motor windings. H-bridge includes circuitry to regulate or limit the winding current.

With proper PCB design, H-bridge of the SGM42609 is capable of driving up to 1.5A RMS (or DC) continuously, at +25°C with a V_{CC} supply of 5V. It can support peak current of up to 2A. Current capability is reduced slightly at lower V_{CC} voltage.

Internal shutdown functions with a fault output pin are provided for H-bridge over-current protection, power supply under-voltage lockout, charge pump undervoltage lockout and over-temperature protection. If one of fault conditions happens, the SGM42609 would prevent each input PWM signal from driving H-bridge and H-bridge is in high impedance status.

A low-power sleep mode is also provided to save power dissipation. If both IN1 and IN2 are low for more than t_{sleep} , the SGM42609 will enter into sleep state automatically.

The SGM42609 is available in Green MSOP-10 and TDFN-3×3-10L packages. It operates over an ambient temperature range of -40°C to +125°C.

FEATURES

- Single H-Bridge Motor Driver can Drive One DC Brush Motor
- Low MOSFET On-Resistance: HS + LS 480mΩ
- Output Current 1.5A RMS, 2A Peak Current (at V_{cc} = 5V, +25°C)
- 2.7V to 24V Wide Power Supply Voltage Range
- PWM Winding Current Regulation/Limiting
- Fault Indication Output
- Available in Green MSOP-10 and TDFN-3×3-10L Packages

APPLICATIONS

Battery-Powered Toys Toothbrushes Video Security Cameras Office Automation Machines Gaming Machines Robotics



PACKAGE/ORDERING INFORMATION

MODEL	PACKAGE DESCRIPTION	SPECIFIED TEMPERATURE RANGE	ORDERING NUMBER	PACKAGE MARKING	PACKING OPTION
SGM42609	MSOP-10	-40°C to +125°C	SGM42609XMS10G/TR	SGM42609 XMS10 XXXXX	Tape and Reel, 4000
301142009	TDFN-3×3-10L	-40°C to +125°C	SGM42609XTD10G/TR	SGM 42609D XXXXX	Tape and Reel, 4000

NOTE: XXXXX = Date Code and Vendor Code.

Green (RoHS & HSF): SG Micro Corp defines "Green" to mean Pb-Free (RoHS compatible) and free of halogen substances. If you have additional comments or questions, please contact your SGMICRO representative directly.

ABSOLUTE MAXIMUM RATINGS

Power Supply Voltage Range, V _{CC}	0.3V to 26.5V
Digital Input Pin Voltage Range	0.3V to 6V
ISEN Pin Voltage Range	0.3V to 0.5V
Peak Motor Drive Output Current	Internally Limited
Package Thermal Resistance	
MSOP-10, θ _{JA}	175°C/W
TDFN-3×3-10L, θ _{JA}	80°C/W
Junction Temperature	+150°C
Storage Temperature Range	65°C to +150°C
Lead Temperature (Soldering, 10sec)	+260°C
ESD Susceptibility	
HBM	5000V
MM	300V
CDM	1000V

RECOMMENDED OPERATING CONDITIONS

Power Supply Voltage Range, V _{CC}	2.7V to 24V
Digital Input Pin Voltage Range	0V to 5.5V
Continuous DC/RMS Output Current	1.5A
Operating Temperature Range	40°C to +125°C

OVERSTRESS CAUTION

Stresses beyond those listed may cause permanent damage to the device. Functional operation of the device at these or any other conditions beyond those indicated in the operational section of the specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

ESD SENSITIVITY CAUTION

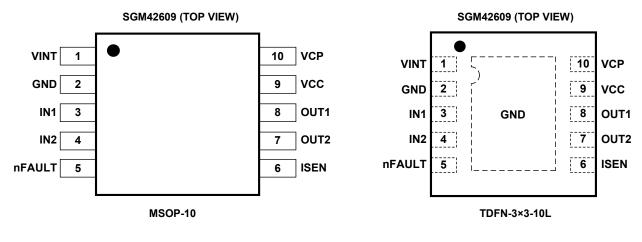
This integrated circuit can be damaged by ESD if you don't pay attention to ESD protection. SGMICRO recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage. ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

DISCLAIMER

SG Micro Corp reserves the right to make any change in circuit design, specification or other related things if necessary without notice at any time.



PIN CONFIGURATIONS



PIN DESCRIPTION

	PIN	NAME	I/O	FUNCTION		
MSOP-10	TDFN-3×3-10L	NAME	1/O	FUNCTION		
1	1	VINT	_	Internal Supply Bypass. Bypass to GND with 2.2µF, 6.3V capacitor.		
2	2	GND	G	Ground. Both the GND pin and device exposed pad must be connected to ground.		
3	3	IN1	-	Bridge Input 1. Logic input controls state of OUT1. Internal pull-down.		
4	4	IN2	Ι	Bridge Input 2. Logic input controls state of OUT2. Internal pull-down.		
5	5	nFAULT	OD	Fault Output. Logic low when in fault condition (over-temperature, over-current, power supply under-voltage, charge pump under-voltage).		
6	6	ISEN	10	Bridge Ground or I _{SENSE} . Connect to current sense resistor for bridge, or GND if current control not needed.		
7	7	OUT2	0	Bridge Output 2. Connect to motor winding.		
8	8	OUT1	0	Bridge Output 1. Connect to motor winding.		
9	9	VCC	Ρ	Device Power Supply. Connect to motor supply. A 10µF (MIN) ceramic bypass capacitor to GND is recommended.		
10	10	VCP	10	High-side Gate Drive Voltage. Connect a $0.01\mu F$, $30V$ (MIN) ceramic capacitor to VCC.		
_	Exposed Pad	GND	G	Exposed Pad. Exposed pad is internally connected to GND. Connect it to a large ground plane to maximize thermal performance; not intended as an electrical connection point.		

NOTE: I = input; O = output; IO = input or output; OD = open-drain output; G: ground; P: power for the circuit.



ELECTRICAL CHARACTERISTICS

(V_{CC} = 5V, Full = -40°C to +125°C. Typical values are at T_A = +25°C, unless otherwise noted.)

PARAMETER	SYMBOL	CONDITIONS	TEMP	MIN	TYP	MAX	UNITS	
POWER SUPPLIES		-						
VCC Operating Supply Voltage	V _{cc}		Full	2.7		24	V	
VCC Operating Supply Current	I _{VCC}	IN1 = 0V, IN2 = 0V (less than t_{sleep})	+25°C		1.5	2	mA	
VCC Sleep Mode Supply Current	Ivccq	IN1 = 0V, IN2 = 0V (more than t_{sleep})	+25°C		0.9	2.5	μA	
Enter Sleep Mode Time	t _{sleep}	IN1 = 0V, IN2 = 0V	+25°C	5.2	6.2	7.4	S	
VCC Under-Voltage Lockout Voltage	V _{UVLO}		+25°C		2.3	2.4	V	
VCC Under-Voltage Lockout Voltage Hysteresis	V _{HYS}		+25°C		100		mV	
LOGIC LEVEL INPUTS								
Input Low Voltage	V _{IL}	V _{CC} = 2.7V to 24V	Full			0.7	V	
Input High Voltage	V _{IH}	V_{CC} = 2.7V to 24V	Full	2.3			V	
Input Hysteresis	V _{HYS}		+25°C		200		mV	
Input Pull-Down Resistance	R _{PD}		+25°C		160		kΩ	
Input Low Current	I _{IL}	$V_{IN} = 0V$	Full	-1		1	μA	
Input High Current	I _{IH}	V _{IN} = 5V	Full		35	48	μA	
Input Deglitch Time	t _{DEG}	V _{IN} = 5V	+25°C		460		ns	
nFAULT OUTPUT (OPEN-DRAIN O	UTPUT)							
Output Low Voltage	V _{OL}	V _{IN} = 2V, I _O = -5mA	+25°C			0.52	V	
Output High-Impedance Leakage Current	I _{он}		+25°C			1	μA	
H-BRIDGE FETS		•						
		V _{CC} = 5V, I _O = 200mA	+25°C		260			
		V _{CC} = 5V, I _O = 200mA	Full			545	mΩ	
HS FET On-Resistance	R _{DS(ON)}	V _{CC} = 2.7V, I _O = 200mA	+25°C		320			
		V _{CC} = 2.7V, I _O = 200mA	Full			635		
		V _{CC} = 5V, I _O = -200mA	+25°C		220			
		V _{CC} = 5V, I _O = -200mA	Full			510		
LS FET On-Resistance	R _{DS(ON)}	V _{CC} = 2.7V, I _O = -200mA	+25°C		260		mΩ	
		V _{CC} = 2.7V, I _O = -200mA	Full			590	590	
Off-State Leakage Current	I _{OFF}	V _{CC} = 26.5V, V _{OUT} = 0V	+25°C	-1.5		1.5	μA	
MOTOR DRIVER		·						
Current Control PWM Frequency	f _{PWM}	Internal PWM Frequency	+25°C		45		kHz	
Rise Time	t _R	R_L = 16 Ω to GND, 10% to 90% V _{CC}	+25°C		130		ns	
Fall Time	t _F	R_L = 16 Ω to V _{CC} , 90% to 10% V _{CC}	+25°C		120		ns	
Propagation Delay INx to OUTx	t _{PROP}		+25°C		1.2		μs	
Dead Time ⁽¹⁾	t _{DEAD}		+25°C		550		ns	

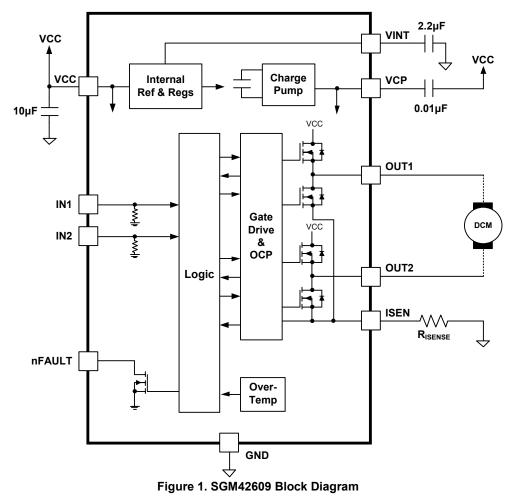
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ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	CONDITIONS	TEMP	MIN	TYP	MAX	UNITS
PROTECTION CIRCUITS		•					
Over-Current Protection Trip Level	I _{OCP}		+25°C	2.5	3.3		А
OCP Deglitch Time	t _{DEG}		+25°C		4		μs
Over-Current Protection Period	t _{OCP}		+25°C		1.4		ms
Thermal Shutdown Temperature	T _{TSD}	Die Temperature			160		°C
Thermal Shutdown Temperature Hysteresis	T _{HYS}				30		°C
CURRENT CONTROL							
ISEN Trip Voltage	V _{TRIP}		+25°C	150	200	260	mV
Current Sense Blanking Time	t _{BLANK}		+25°C		4		μs
SLEEP MODE	•	·	•		•	•	
Start-Up Time	t _{WAKE}	nSleep inactive high to H-bridge on	+25°C			1.4	ms

NOTE: 1. Internal dead time. External implementation is not necessary.

FUNCTIONAL BLOCK DIAGRAM



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DETAILED DESCRIPTION

PWM Motor Drivers

The SGM42609 contains one H-bridge motor driver with current-control PWM circuitry. A block diagram of the circuitry is shown below:

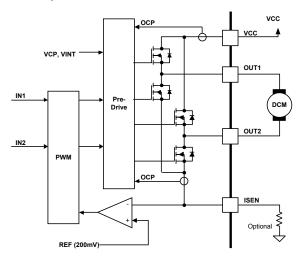


Figure 2. Motor Control Circuitry

Bridge Control and Decay Modes

The IN1 and IN2 input pins control the state of the OUT1 and OUT2 outputs. Table 1 shows the logic.

Table	1.	H-Bridge	Logic
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IN1	IN2	OUT1	OUT2	FUNCTION	NOTES
0	0	Z	Z	Sleep	Both IN1 & IN2 are low more than t _{sleep} .
0	0	Z	Z	Coast	Both IN1 & IN2 are low less than t _{sleep} .
0	1	L	Н	Reverse	
1	0	н	L	Forward	
1	1	L	L	Brake/Slow Decay	

When both IN1 and IN2 are low more than t_{sleep} , the device will into a low-power sleep state. When both IN1 and IN2 are low less than t_{sleep} , the device will be at coast state. The inputs can also be used for PWM control of the motor speed. When controlling a winding with PWM, when the drive current is interrupted, the inductive nature of the motor requires that the current must continue to flow. This is called recirculation current. To handle this recirculation current, the H-bridge can operate in two different states, fast decay or slow decay. In fast decay mode, the H-bridge is disabled and recirculation current flows through the

body diodes; in slow decay, the motor winding is shorted.

To PWM using fast decay, the PWM signal is applied to one IN pin while the other is held low; to use slow decay, one IN pin is held high.

Table 2. PWM Control of Motor Speed

IN1	IN2	FUNCTION			
PWM	0	Forward PWM, Fast Decay			
1	PWM	Forward PWM, Slow Decay			
0	PWM	Reverse PWM, Fast Decay			
PWM	1	Reverse PWM, Slow Decay			

Figure 3 shows the current paths in different drive and decay modes.

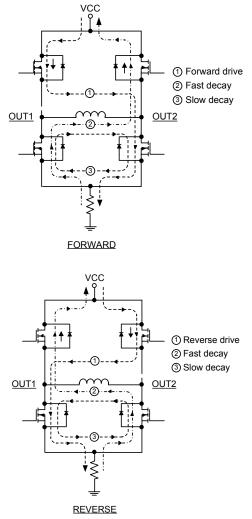


Figure 3. Decay Modes

DETAILED DESCRIPTION (continued)

Current Control

The current through the motor windings may be limited, or controlled, by a fixed-frequency PWM current regulation, or current chopping. For DC motors, current control is used to limit the start-up and stall current of the motor.

When an H-bridge is enabled, current rises through the winding at a rate dependent on the DC voltage and inductance of the winding. If the current reaches the current chopping threshold, the bridge disables the current until the beginning of the next PWM cycle. Note that immediately after the current is enabled, the voltage on the ISEN pin is ignored for a fixed period of time before enabling the current sense circuitry. This blanking time is fixed at 4μ s. This blanking time also sets the minimum on time of the PWM when operating in current chopping mode.

The PWM chopping current is set by a comparator which compares the voltage across a current sense resistor connected to the ISEN pin with a reference voltage. The reference voltage is fixed at 200mV. The chopping current is calculated in Equation 1.

$$I_{CHOP} = \frac{200 \text{mV}}{\text{R}_{\text{ISENSE}}}$$
(1)

For example:

If a 1Ω sense resistor is used, the chopping current will be $200\text{mV}/1\Omega = 200\text{mA}$. Once the chopping current threshold is reached, the H-bridge switches to slow decay mode. Winding current is re-circulated by enabling both of the low-side FETs in the bridge. This state is held until the beginning of the next fixed-frequency PWM cycle.

Note that if current control is not needed, the ISEN pin should be connected directly to ground.

Sleep Operation

After both IN1 and IN2 are low more than t_{sleep} , the output drivers are disabled and the device is placed into a low-power sleep state. In this state, the H-bridge is

disabled, the gate drive charge pump is stopped, all internal logic is reset, and all internal clocks are stopped. When returning from sleep mode, some time (up to 1.4ms) needs to pass before the motor driver becomes fully operational.

Over-Current Protection (OCP)

An analog current limit circuit on each FET limits the current through the FET by limiting the gate drive. If this analog current limit persists for longer than the OCP deglitch time, all FETs in the H-bridge will be disabled and the nFAULT pin will be driven low. The driver will be re-enabled after the OCP retry period (t_{OCP}) has passed. nFAULT becomes high again at this time. If the fault condition is still present, the cycle repeats. If the fault is no longer present, normal operation resumes and nFAULT remains deasserted.

Over-current conditions are detected independently on both high and low side devices; i.e., a short across the motor winding will all result in an over-current shutdown. Note that over-current protection does not use the current sense circuitry used for PWM current control, so functions even without presence of the ISEN resistors.

Thermal Shutdown (TSD)

If the die temperature exceeds safe limits, all FETs in the H-bridge will be disabled and the nFAULT pin will be driven low. Once the die temperature has fallen to a safe level operation will automatically resume.

Under-Voltage Lockout (UVLO)

If at any time the voltage on the VCC pin falls below the under-voltage lockout threshold voltage, all circuitry in the device will be disabled, and all internal logic will be reset. Operation will resume when V_{CC} rises above the UVLO threshold. nFAULT is driven low in the event of an under-voltage condition.



APPLICATION INFORMATION

Maximum Output Current

In actual operation, the maximum output current achievable with a motor driver is a function of die temperature.

This in turn is greatly affected by ambient temperature and PCB design. Basically, the maximum motor current will be the amount of current that results in a power dissipation level that, along with the thermal resistance of the package and PCB, keeps the die at a low enough temperature to stay out of thermal shutdown.

The dissipation ratings given in the datasheet can be used as a guide to calculate the approximate maximum power dissipation that can be expected to be possible without entering thermal shutdown for several different PCB constructions. However, for accurate data, the actual PCB design must be analyzed via measurement or thermal simulation.

Power Dissipation

Power dissipation in the SGM42609 is dominated by the DC power dissipated in the output FET resistance. There is additional power dissipated due to PWM switching losses, which are dependent on PWM frequency, rise and fall times, and VCC power supply voltage. These switching losses are typically on the order of 10% to 30% of the DC power dissipation.

The DC power dissipation of H-bridge can be roughly estimated by Equation 2.

 $\mathsf{P}_{\mathsf{TOT}} = (\mathsf{HS} - \mathsf{R}_{\mathsf{DS}(\mathsf{ON})} \times \mathsf{I}_{\mathsf{OUT}(\mathsf{RMS})}^{2}) + (\mathsf{LS} - \mathsf{R}_{\mathsf{DS}(\mathsf{ON})} \times \mathsf{I}_{\mathsf{OUT}(\mathsf{RMS})}^{2})$

where P_{TOT} is the total power dissipation, HS - $R_{DS(ON)}$ is the resistance of the high side FET, LS - $R_{DS(ON)}$ is the resistance of the low side FET, and $I_{OUT(RMS)}$ is the RMS output current being applied to the motor.

Note that $R_{DS(ON)}$ increases with temperature, so as the device heats, the power dissipation increases. This must be taken into consideration when sizing the heatsink.

Thermal Protection

Any tendency of the device to enter TSD is an indication of either excessive power dissipation, insufficient heatsinking, or too high an ambient temperature.

Heatsinking

The TDFN-3×3-10L package uses an exposed pad to remove heat from the device. For proper operation, this pad must be thermally connected to copper on the PCB to dissipate heat. On a multi-layer PCB with a ground plane, this can be accomplished by adding a number of vias to connect the thermal pad to the ground plane. On PCBs without internal planes, copper area can be added on either side of the PCB to dissipate heat. If the copper area is on the opposite side of the PCB from the device, thermal vias are used to transfer the heat between top and bottom layers.

REVISION HISTORY

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

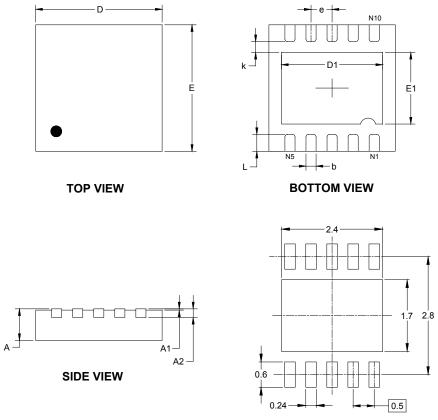
Changes from Original (JUNE 2017) to REV.A

Changed from product preview to production data.....All



PACKAGE OUTLINE DIMENSIONS

TDFN-3×3-10L



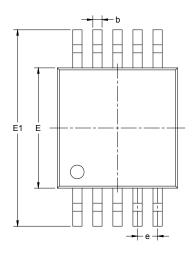
RECOMMENDED LAND PATTERN (Unit: mm)

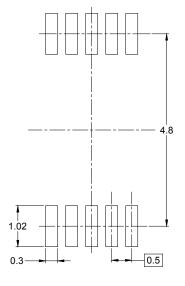
Symbol		nsions meters	Dimensions In Inches		
5	MIN	MAX	MIN	MAX	
A	0.700	0.800	0.028	0.031	
A1	0.000	0.050	0.000	0.002	
A2	0.203	3 REF	0.008 REF		
D	2.900	3.100	0.114	0.122	
D1	2.300	2.600	0.091	0.103	
E	2.900	3.100	0.114	0.122	
E1	1.500	1.800	0.059	0.071	
k	0.200) MIN	0.008	3 MIN	
b	0.180	0.300	0.007	0.012	
е	0.500	0.500 TYP		TYP	
L	0.300	0.500	0.012	0.020	



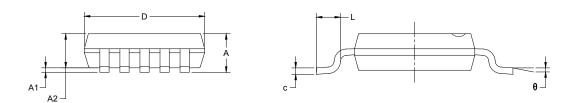
PACKAGE OUTLINE DIMENSIONS

MSOP-10





RECOMMENDED LAND PATTERN (Unit: mm)

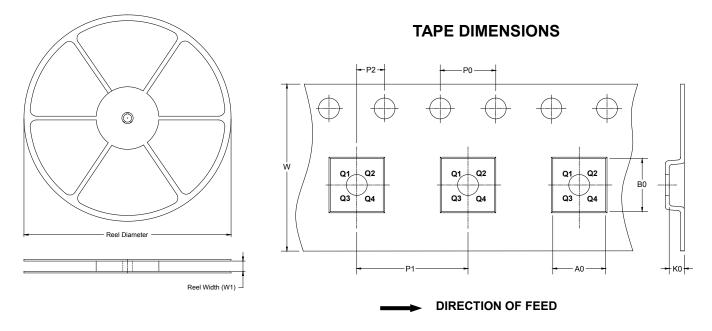


Symbol		nsions meters	Dimensions In Inches		
	MIN	MAX	MIN	MAX	
A	0.820	1.100	0.032	0.043	
A1	0.020	0.150	0.001	0.006	
A2	0.750	0.950	0.030	0.037	
b	0.180	0.280	0.007	0.011	
С	0.090	0.230	0.004	0.009	
D	2.900	3.100	0.114	0.122	
E	2.900	3.100	0.114	0.122	
E1	4.750	5.050	0.187	0.199	
е	0.500	0.500 BSC		BSC	
L	0.400	0.800	0.016	0.031	
θ	0°	6°	0°	6°	



TAPE AND REEL INFORMATION

REEL DIMENSIONS

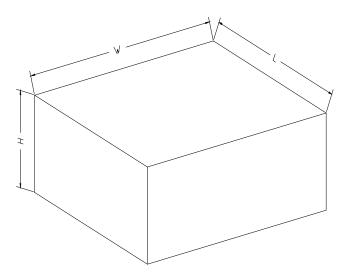


NOTE: The picture is only for reference. Please make the object as the standard.

KEY PARAMETER LIST OF TAPE AND REEL

Package Type	Reel Diameter	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P0 (mm)	P1 (mm)	P2 (mm)	W (mm)	Pin1 Quadrant
MSOP-10	13″	12.4	5.20	3.30	1.20	4.0	8.0	2.0	12.0	Q1
TDFN-3×3-10L	13″	12.4	3.35	3.35	1.13	4.0	8.0	2.0	12.0	Q1

CARTON BOX DIMENSIONS



NOTE: The picture is only for reference. Please make the object as the standard.

KEY PARAMETER LIST OF CARTON BOX

Reel Type	Length (mm)	Width (mm)	Height (mm)	Pizza/Carton	
13″	386	280	370	5	DD0002

